

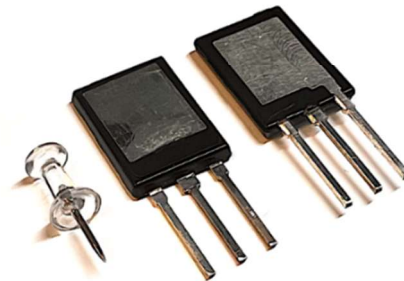
M3S

400kW (420A 800V) 3-Phase Power Stack
1200V SiC die; 4 per switch
0.1°C/W R_{TH} 2nH L_{par}

0.6 kg
0.28 L
126 x 44 x 64mm

Each switch consists of one non-isolated Power Modules, with both sides (Drain & Source) electrically live.

POWER MODULE PARAMETER	VALUE
Number of SiC die	Up to 4
Thermal Resistance ($R_{th,j-c}$)	< 0.02 °C/W
Inductance (L_{par})	< 1nH
Continuous Current (Max)	420 A
Static $R_{DS(on)}$ @ 25°C	4.0 mΩ
Static $R_{DS(on)}$ @ 200°C	7.5 mΩ



2 patents issued
2 pending

The M3S consists of two Power Modules per phase, in a 3-phase configuration.

M3S POWER STACK PARAMETER	VALUE	CONDITIONS
Continuous Drain Current (Max)	420 A	$T_F = 65^\circ\text{C}$; 10L/min coolant flow
Thermal Resistance ($R_{TH,j-f}$)	< 0.1 °C/W	Junction to Fluid; 10L/min coolant flow
Inductance (L_{par})	<2nH	V- to V+
Static $R_{DS(on)}$ @ 25°C	4.0 mΩ	$V_{GS} = 18\text{V}$, $I_D = 240\text{A}$
Static $R_{DS(on)}$ @ 200°C	7.5 mΩ	$V_{GS} = 18\text{V}$, $I_D = 240\text{A}$
Turn-On Switching Energy (E_{ON})	4.0 mJ	$V_{DD} = 800\text{V}$, $I_D = 240\text{A}$
Turn-Off Switching Energy (E_{OFF})	2.7 mJ	$V_{DD} = 800\text{V}$, $I_D = 240\text{A}$
Reverse Recovery Time (t_{rr})	25 ns	$V_{DD} = 800\text{V}$, $I_D = 240\text{A}$
Reverse Diode V_F @ 480A	5.2 V	$V_{GS} = -5\text{V}$

*Values will vary depending on the die used.

APPLICATIONS

- Power Conversion across Automotive, Industrial, Defense, Data Centers, Renewable, Grid, etc.

BENEFITS

- Ultra-compact, high-density 3-phase power stack.
- Fast switching, with industry-leading thermal performance. (<0.1°C/W) and ultra-low parasitic inductance (<2nH).
- Can use any supplier's SiC, IGBT, or both.
- 75% smaller 50% lighter converter with 30% fewer dies.
- Scalable - M3D (800kW) and M3Q (1600kW).

FEATURES

- Gate driver board available.
- Eval Kit available (with 800V 320uF bulk cap).
- 5.5uF close-coupled snubber caps per phase available.



6 patents issued
3 pending

OPTIONS TO LICENSE IP OR PURCHASE PRODUCT